

Antti Rantamäki

List of Publications by Year in descending order

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15
papers

353
citations

933264

10
h-index

1125617

13
g-index

16
all docs

16
docs citations

16
times ranked

258
citing authors

#	ARTICLE	IF	CITATIONS
1	Lattice-Matched GaSb SESAMs for Ultrafast Infrared Lasers. , 2018, , .		0
2	134-µm VECSEL mode-locked with a GaSb-based SESAM. Optics Letters, 2018, 43, 3353.	1.7	10
3	Optically pumped VECSELS: review of technology and progress. Journal Physics D: Applied Physics, 2017, 50, 383001.	1.3	165
4	Thermal Management in Long-Wavelength Flip-Chip Semiconductor Disk Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 336-342.	1.9	12
5	Towards high power flip-chip long-wavelength semiconductor disk lasers. Proceedings of SPIE, 2015, , .	0.8	2
6	750-nm 15-W frequency-doubled semiconductor disk laser with a 44-nm tuning range. Optics Letters, 2015, 40, 4380.	1.7	12
7	High-power flip-chip semiconductor disk laser in the 13-µm wavelength band. Optics Letters, 2014, 39, 4855.	1.7	13
8	High power semiconductor disk laser with a semiconductor-dielectric-metal compound mirror. Applied Physics Letters, 2014, 104, .	1.5	14
9	Wafer-fused VECSELS emitting in the 1310nm waveband. , 2014, , .		2
10	Low Temperature Gold-to-Gold Bonded Semiconductor Disk Laser. IEEE Photonics Technology Letters, 2013, 25, 1062-1065.	1.3	18
11	156 µm 1 watt single frequency semiconductor disk laser. Optics Express, 2013, 21, 2355.	1.7	14
12	Multi-Watt Semiconductor Disk Laser by Low Temperature Wafer Bonding. IEEE Photonics Technology Letters, 2013, 25, 2233-2235.	1.3	10
13	1 W at 785 nm from a frequency-doubled wafer-fused semiconductor disk laser. Optics Express, 2012, 20, 9046.	1.7	26
14	4.6-W Single Frequency Semiconductor Disk Laser With 75 kHz Linewidth. IEEE Photonics Technology Letters, 2012, 24, 1378-1380.	1.3	14
15	3 W of 650 nm red emission by frequency doubling of wafer-fused semiconductor disk laser. Optics Express, 2010, 18, 21645.	1.7	41